

## Nonequilibrium diffusion of reactive solid islands

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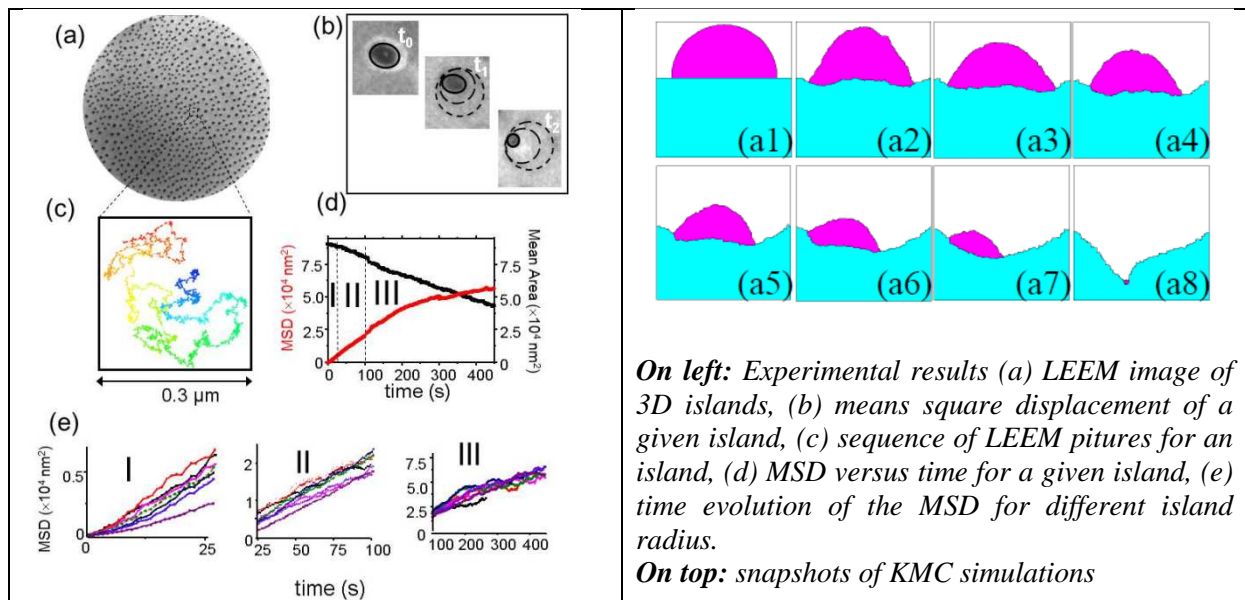
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In this paper we report on the combined effects of reactivity, wetting, and shape changes on the random motion of crystalline Si islands on amorphous SiO<sub>2</sub> substrates during annealing. For this purpose nanoparticle motion and size evolution are studied both experimentally (*in situ* and real time experiments) and theoretically [kinetic Monte Carlo simulations (KMC) including chemical reactivity). We show that the time dependence of the mean square displacement behaviors: (I) an equilibrium Brownian motion consistent with existing equilibrium theories, leading to strong size dependence of the diffusion constant, (II) an unexpected regime characterized by a linear time dependence of the MSD roughly independent on the nanoparticle size, attributed to a repeated pinning depinning of the triple line in ring-shape trenches formed by chemical reaction, and (III) a self-trapping regime where the reactive islands are trapped in the pit they drill in the substrate, leading to a saturation of the MSD.

The experimental observations are supported by the KMC simulations, based on interface reaction of Si with SiO<sub>2</sub>, interface diffusion of oxygen, and evaporation of SiO.



### Reference:

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